



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

NANDAKUMAR

Serial No. 09/252,514 (TI-23103)

Filed February 18, 1999

For: DUAL-COUNTERDOPED CHANNEL FIELD EFFECT TRANSISTOR AND METHOD

Art Unit 2811

Examiner S. Crane

Commissioner for Patents  
Washington, D. C. 20231

Sir:

**AMENDMENT UNDER 37 C.F.R. 1.116**

In response to the Office action dated February 15, 2001, please amend the above identified application as follows:

**In the claims:**

Amend claim 1 as follows:

1. (Twice Amended) A field effect transistor comprising:  
a region of semiconductor material doped a first conductivity type;  
a source of [opposite] first conductivity type and a drain of [opposite] said first  
conductivity type, both said source and said drain disposed in said region of semiconductor  
material and separated by a counterdoped channel region disposed in said region of  
semiconductor material;

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FEB 28 2001  
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Amend  
7/13/01  
Jules  
3/2/01  
SC/MS